

2SK3080

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

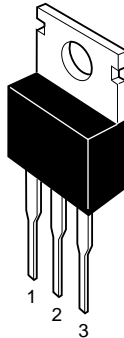
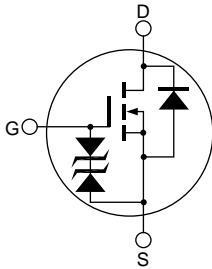
ADE-208-635A (Z)
2nd. Edition
May 1998

Features

- Low on-resistance
 $R_{DS(on)} = 20 \text{ m}\Omega$ typ. ($V_{GS} = 10\text{V}$, $I_D = 15 \text{ A}$)
- 4V gate drive devices.
- High speed switching

Outline

TO-220AB



1. Gate
2. Drain(Flange)
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	30	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	120	A
Body-drain diode reverse drain current	I_{DR}	30	A
Channel dissipation	Pch ^{Note2}	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

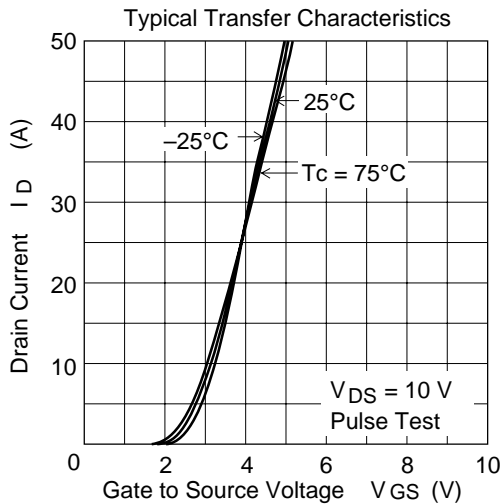
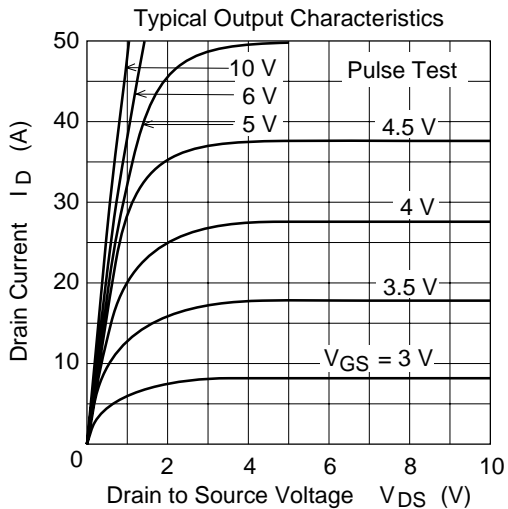
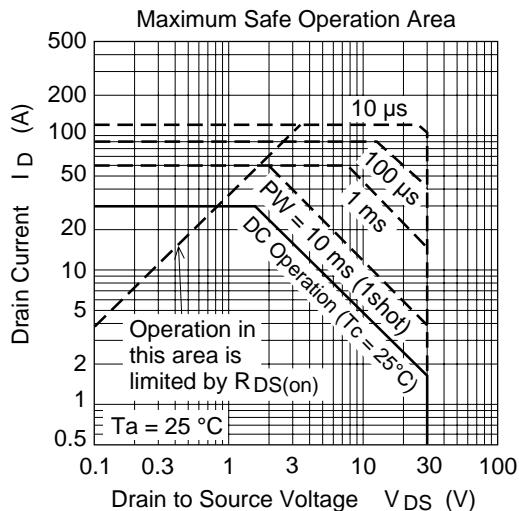
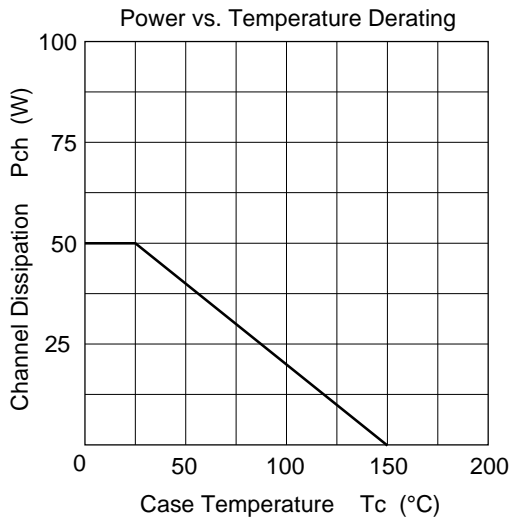
Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

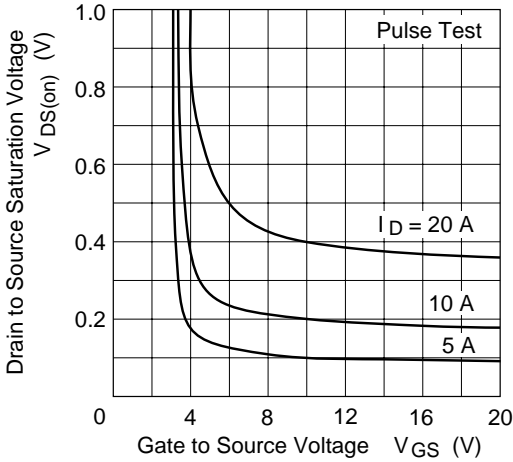
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 30V, V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1mA, V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	20	28	m Ω	$I_D = 15A, V_{GS} = 10V$ ^{Note3}
Static drain to source on state resistance	$R_{DS(on)}$	—	35	50	m Ω	$I_D = 15A, V_{GS} = 4V$ ^{Note3}
Forward transfer admittance	$ y_{fs} $	12	18	—	S	$I_D = 15A, V_{DS} = 10V$ ^{Note3}
Input capacitance	Ciss	—	750	—	pF	$V_{DS} = 10V$
Output capacitance	Coss	—	520	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	210	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$V_{GS} = 10V, I_D = 15A$
Rise time	t_r	—	260	—	ns	$R_L = 0.67\Omega$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	
Fall time	t_f	—	90	—	ns	
Body-drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 30A, V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	45	—	ns	$I_F = 30A, V_{GS} = 0$ $diF/dt = 50A/\mu s$

Note: 3. Pulse test

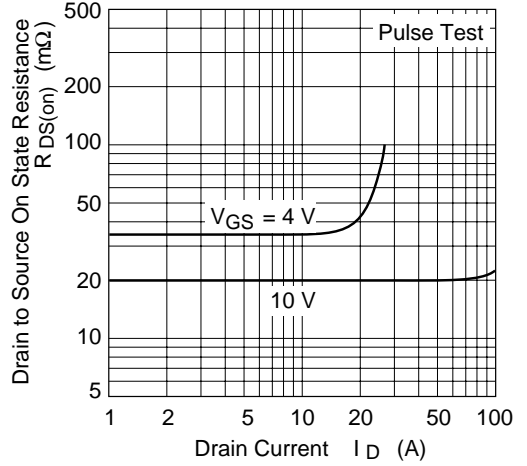
Main Characteristics



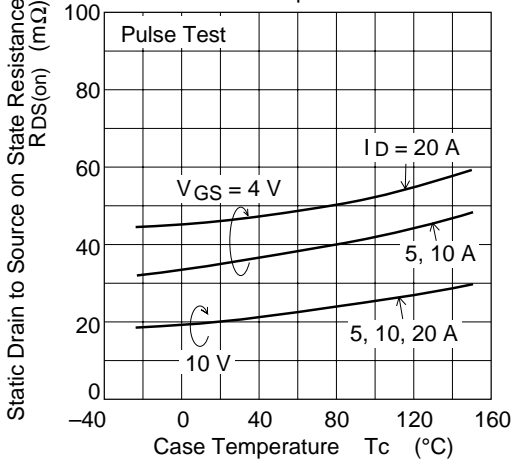
Drain to Source Saturation Voltage vs. Gate to Source Voltage



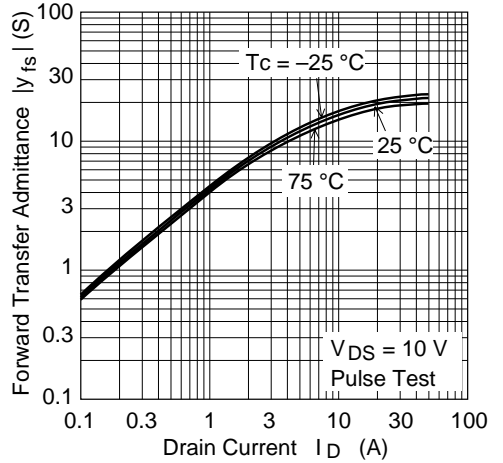
Static Drain to Source on State Resistance vs. Drain Current



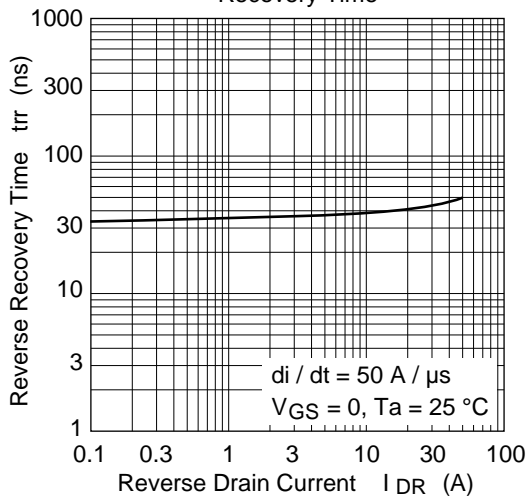
Static Drain to Source on State Resistance vs. Temperature



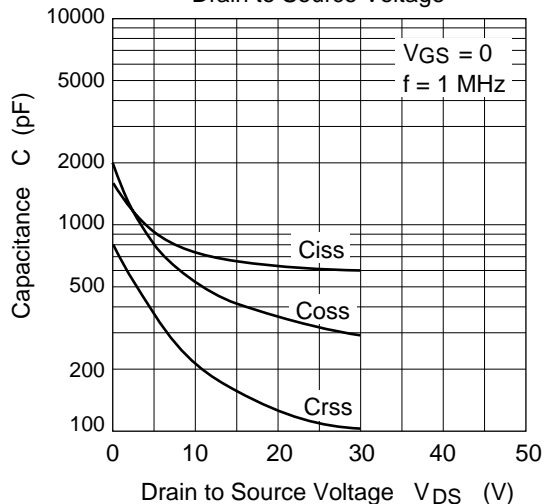
Forward Transfer Admittance vs. Drain Current



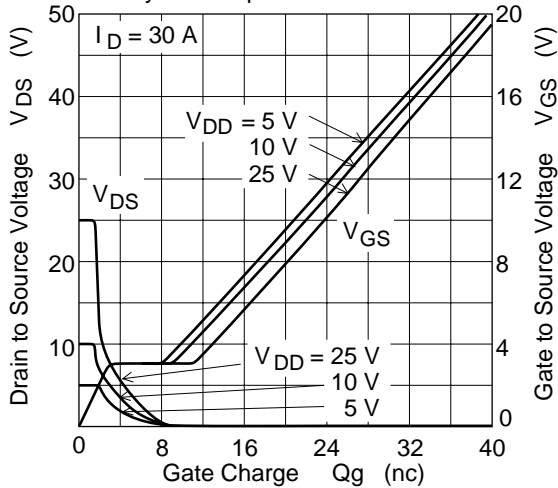
Body-Drain Diode Reverse Recovery Time



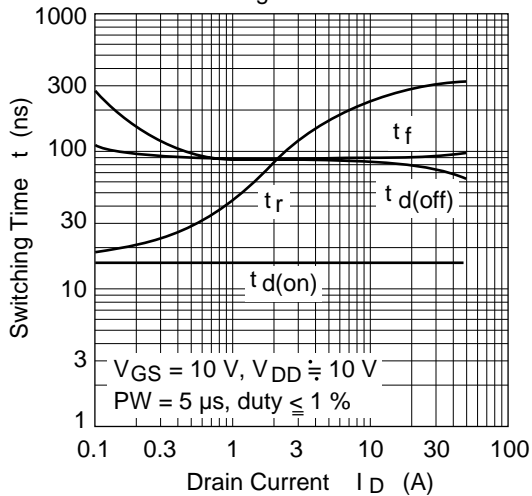
Typical Capacitance vs. Drain to Source Voltage

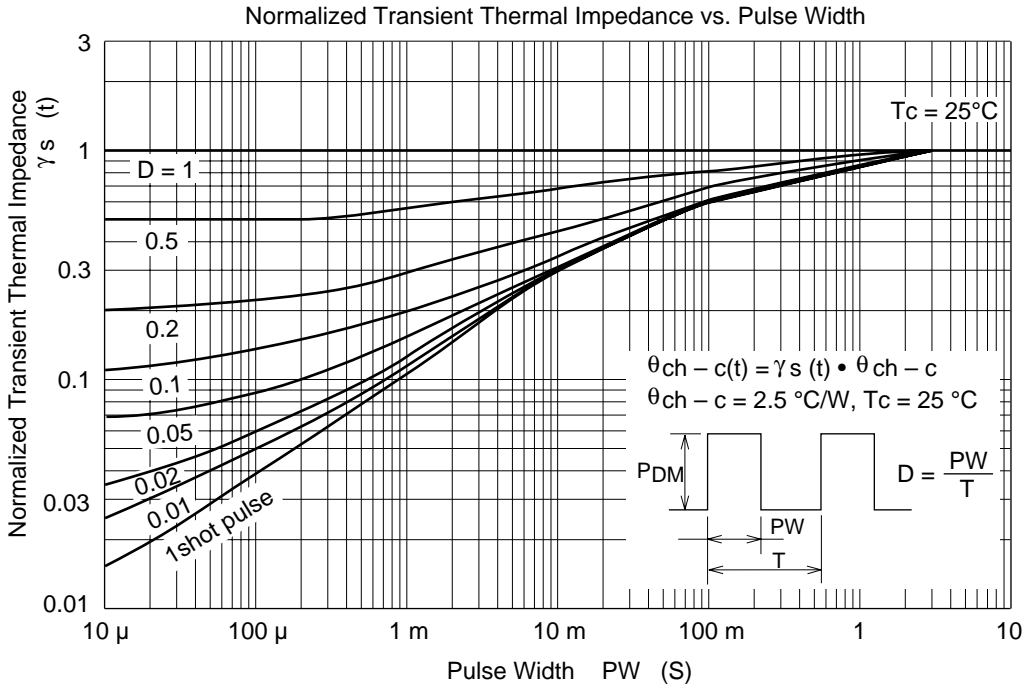
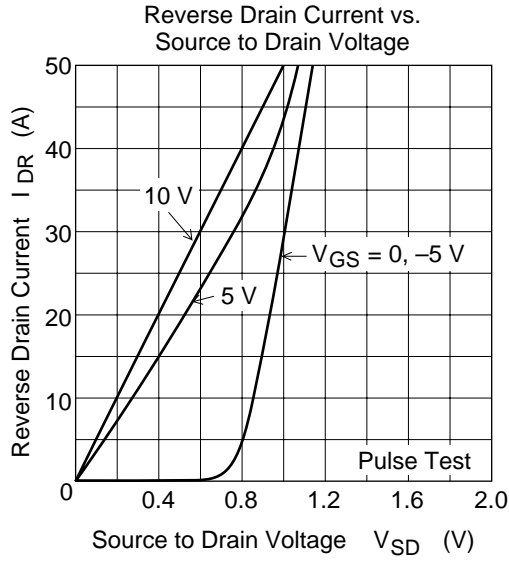


Dynamic Input Characteristics

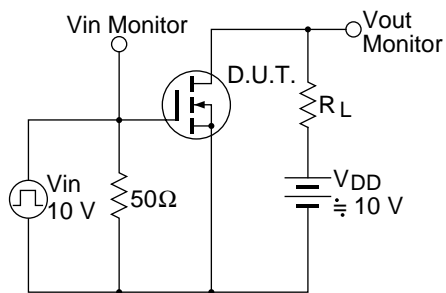


Switching Characteristics

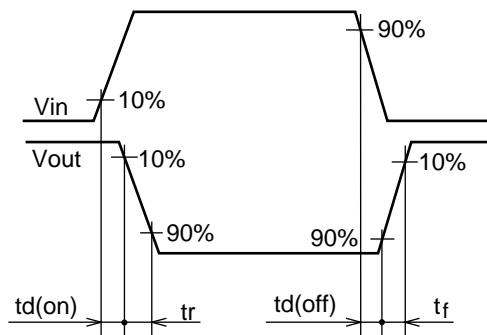




Switching Time Test Circuit

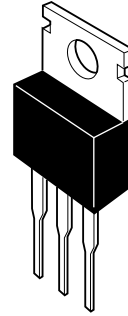
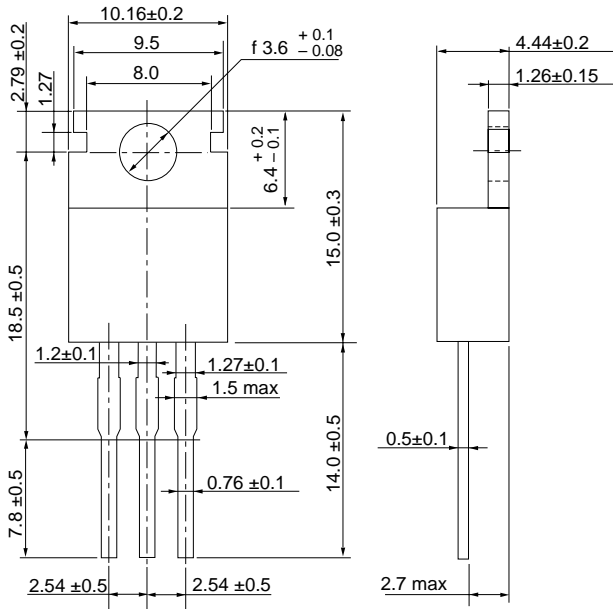


Waveform



Package Dimensions

Unit: mm



Hitachi Code	TO-220AB
EIAJ	SC-46
JEDEC	—

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